

# MMBD914LT1G, SMMBD914LT1G, MMBD914LT3G, SMMBD914LT3G



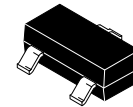
ON Semiconductor®

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## High-Speed Switching Diode

### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



SOT-23  
CASE 318  
STYLE 8

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	100	Vdc
Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

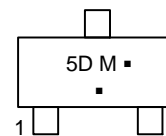


### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### MARKING DIAGRAM



5D = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MMBD914LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD914LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD914LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBD914LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

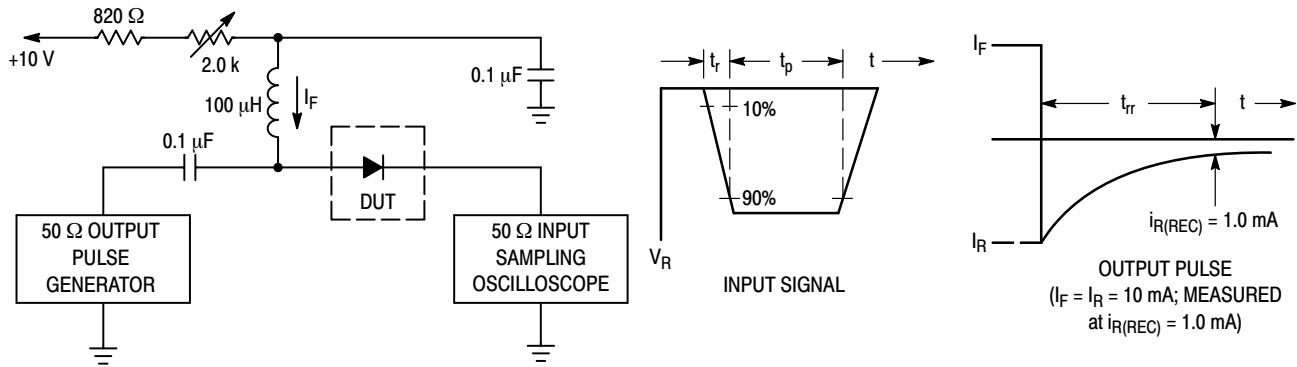
# MMBD914LT1G, SMMBD914LT1G, MMBD914LT3G, SMMBD914LT3G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Reverse Breakdown Voltage ( $I_R = 100 \mu\text{A}$ )	$V_{(BR)}$	100	–	Vdc
Reverse Voltage Leakage Current ( $V_R = 20 \text{ Vdc}$ ) ( $V_R = 75 \text{ Vdc}$ )	$I_R$	– –	25 5.0	nA dc $\mu\text{A}$ dc
Diode Capacitance ( $V_R = 0, f = 1.0 \text{ MHz}$ )	$C_T$	–	4.0	pF
Forward Voltage ( $I_F = 10 \text{ mA}$ )	$V_F$	–	1.0	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mA}$ ) (Figure 1)	$t_{rr}$	–	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

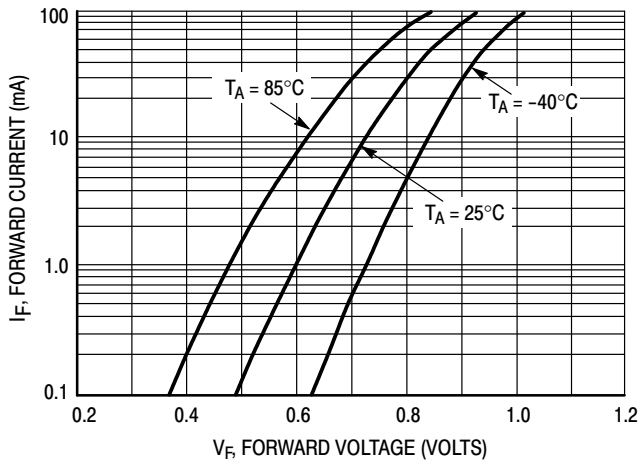
- FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



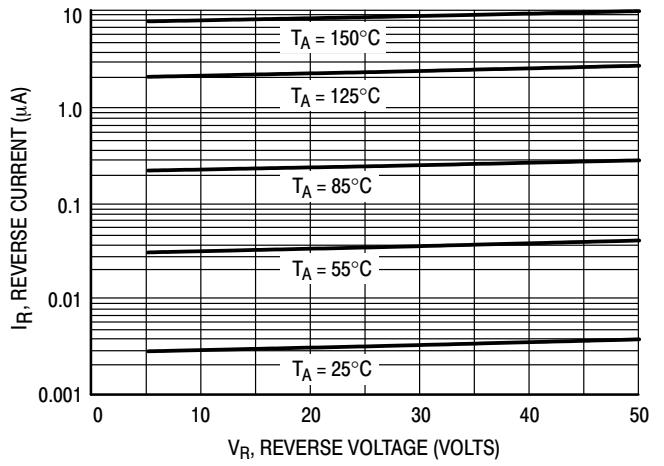
- Notes:
1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.
  2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.
  3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

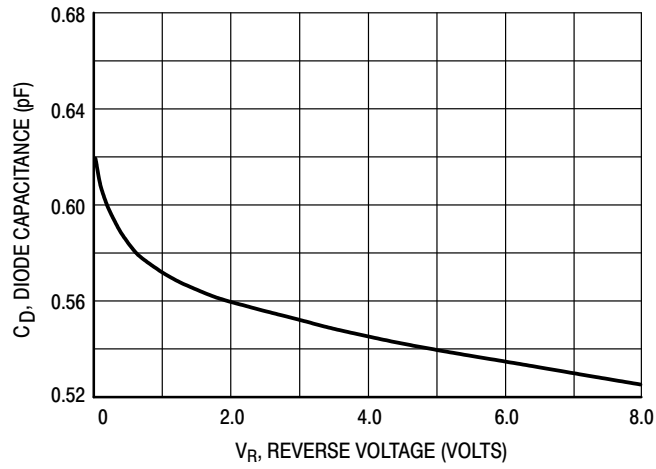
**MMBD914LT1G, SMMBD914LT1G, MMBD914LT3G, SMMBD914LT3G**



**Figure 2. Forward Voltage**



**Figure 3. Leakage Current**



**Figure 4. Capacitance**

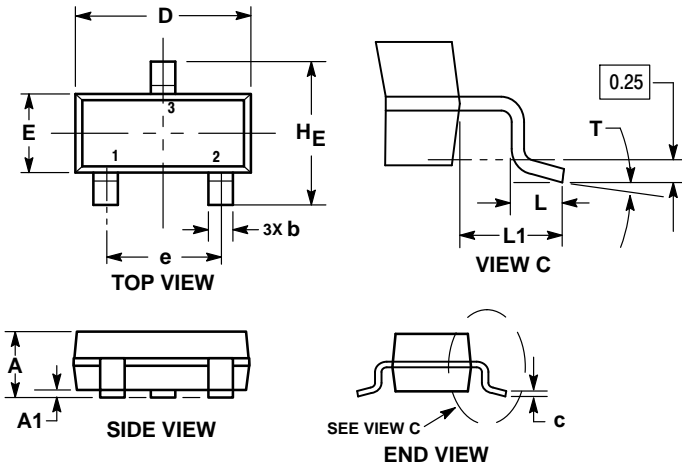
# MMBD914LT1G, SMMBD914LT1G, MMBD914LT3G, SMMBD914LT3G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AR



**NOTES:**

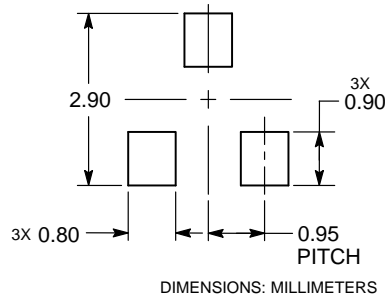
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**STYLE 8:**

1. ANODE
2. NO CONNECTION
3. CATHODE

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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